



### **N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
30V	23mΩ @ V <sub>GS</sub> = 10V	10A
30 V	$33m\Omega$ @ $V_{GS} = 4.5V$	8A

## **Description**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters

### **Features and Benefits**

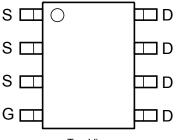
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Low Gate Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

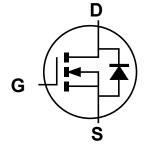
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- · Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.074 grams (approximate)







Top View Internal Schematic



Equivalent circuit

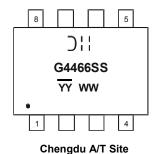
## Ordering Information (Note 4)

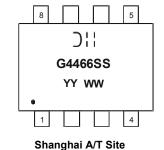
Part Number	Case	Packaging
DMG4466SSSL-13	SO-8	2500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**





);; = Manufacturer's Marking G4466SS = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 13 = 2013) WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characte		Symbol	Value	Unit	
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) Steady $T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$		I <sub>D</sub>	10 6	А	
Pulsed Drain Current (Note 5)			I <sub>DM</sub>	60	A
Avalanche Current (Notes 6)			I <sub>AR</sub>	16	A
Repetitive Avalanche Energy (Notes 6) L = 0.1mH			E <sub>AR</sub>	12.8	mJ

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_{D}$	1.42	W
Thermal Resistance, Junction to Ambient @TA = 25°C (Note 5)	$R_{\theta JA}$	88.4	°C/W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	1.45	2.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Б	_	15	23	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		25	33	11177	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7.5A	
Forward Transfer Admittance	Y <sub>fs</sub>	_	2.5	_	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 10A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.69	1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A	
DYNAMIC CHARACTERISTICS (Note 8)				ı			
Input Capacitance	C <sub>iss</sub>		478.9	_	pF		
Output Capacitance	Coss	_	96.7	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	61.4	_	pF	1 - 1.000112	
Gate Resistance	Rg	0.4	1.1	1.6	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	5.0	8		V - 45V V - 40V I - 40A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	10.5	17	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	1.8	_	nC	$V_{DS} = 15V, V_{GS} = 10V, I_{D} = 10A$	
Gate-Drain Charge	$Q_{gd}$	_	1.6	_	nC	1	
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.9	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	7.9	_	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V,	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	14.6	_	ns	$R_G = 3\Omega, R_L = 1.5\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	3.1	_	ns		

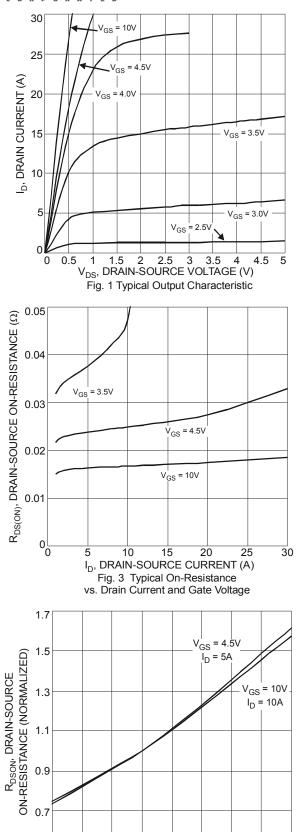
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6.  $I_{AR}$  and  $E_{AR}$  rating are based on low frequency and duty cycles to keep  $T_J$  = 25°C

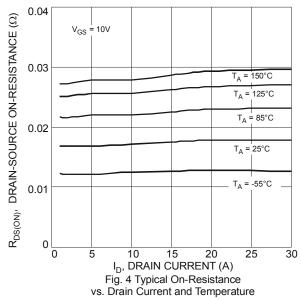
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.





20 V<sub>DS</sub> = 5V 10 V<sub>GS</sub> = 150°C V<sub>GS</sub> = 125°C V<sub>GS</sub> = 25°C V<sub>GS</sub> = -55°C V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Fig. 2 Typical Transfer Characteristic



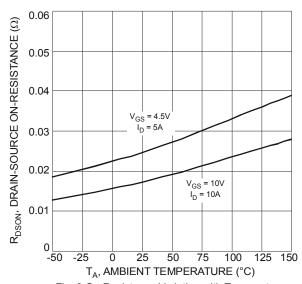


Fig. 6 On-Resistance Variation with Temperature

25

50

T<sub>A</sub>, AMBIENT TEMPERATURE (°C)

Fig. 5 On-Resistance Variation with Temperature

75

100

125 150

0.5 -50

-25



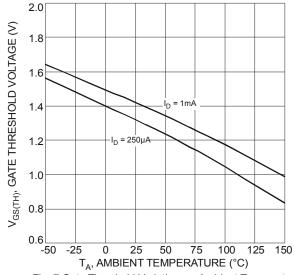
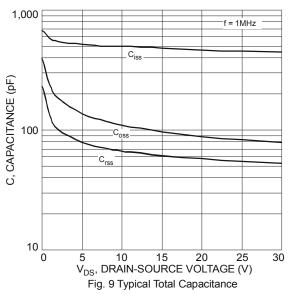
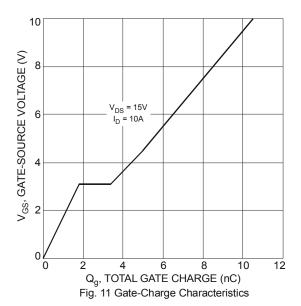
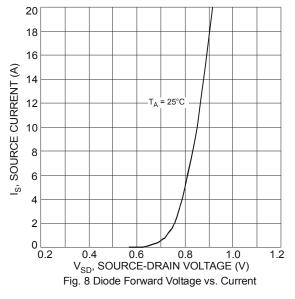
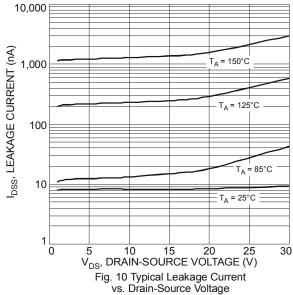


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

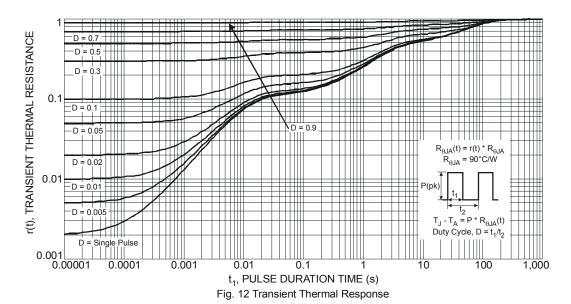






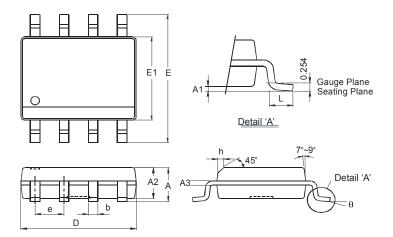






## **Package Outline Dimensions**

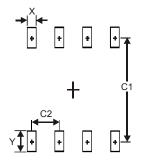
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8					
Dim	Min	Max			
Α	1	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	ı	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)		
X	0.60		
Υ	1.55		
C1	5.4		
C2	1.27		



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